

HFS5N65U

$BV_{DSS} = 650\text{ V}$

$R_{DS(on)\text{ typ}} \leq 1\text{ m}\Omega$

$I_D = 4.5\text{ A}$

Originative New Design
Superior Avalanche Rugged Technology

Package Marking and Ordering Information

Device Marking	Week Marking	Package	Packing	Quantity	RoHS Status
HFS5N65U	YWWX	TO-220F(A)	Tube	50	Pb Free
HFS5N65US	YWWX	TO-220F(B)	Tube	50	Pb Free
HFS5N65U	YWWXg	TO-220F(A)	Tube	50	Halogen Free
HFS5N65US	YWWXg	TO-220F(B)	Tube	50	Halogen Free

* TO-220F(A) : Dual Gauge, TO-220F(B) : Single Gauge

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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On Characteristics

V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.5	--	4.5	V
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 2.25\text{A}$	--	2.3	2.9	$\hat{\Omega}$

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	650	--	--	V
BV_{DSS} / T_J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	--	0.6	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650 \text{ V}$, $V_{GS} = 0 \text{ V}$	--	--	1	μA
		$V_{DS} = 520 \text{ V}$, $T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0 \text{ V}$	--	--	± 100	nA

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1.0 \text{ MHz}$	--	600	780	pF
C_{oss}	Output Capacitance		--	60	78	pF
C_{rss}	Reverse Transfer Capacitance		--	7.7	10	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Time	$V_{DS} = 325 \text{ V}$, $I_D = 4.5 \text{ A}$, $R_G = 25 \hat{\Omega}$ (Note 4,5)	--	22	44	ns
t_r	Turn-On Rise Time		--	40	80	ns
$t_{d(off)}$	Turn-Off Delay Time		--	45	90	ns
t_f	Turn-Off Fall Time		--	35	70	ns
Q_g	Total Gate Charge	$V_{DS} = 520 \text{ V}$, $I_D = 4.5 \text{ A}$, $V_{GS} = 10 \text{ V}$ (Note 4,5)	--	10.5	13.5	nC
Q_{gs}	Gate-Source Charge		--	3.5	--	nC
Q_{gd}	Gate-Drain Charge		--	3	--	nC

Source-Drain Diode Maximum Ratings and Characteristics

I_S	Continuous Source-Drain Diode Forward Current	--	--	4.5	A	
I_{SM}	Pulsed Source-Drain Diode Forward Current	--	--	18		
V_{SD}	Source-Drain Diode Forward Voltage	$I_S = 4.5 \text{ A}$, $V_{GS} = 0 \text{ V}$	--	--	1.4	V
trr	Reverse Recovery Time	$I_S = 4.5 \text{ A}$, $V_{GS} = 0 \text{ V}$ $di_I/dt = 100 \text{ A}/\mu\text{s}$ • (Note 4)	--	243	--	ns
Qrr	Reverse Recovery Charge		--	1.5	--	$\hat{\Omega}$

Notes :

- Repetitive Rating : Pulse width limited by maximum junction temperature
- $L=14.8\text{mH}$, $I_{AS}=4.5\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\text{T}$, Starting $T_J=25^\circ\text{C}$
- $I_{SD}\leq 4.5\text{A}$, $di/dt\leq 100 \text{ A}/\mu\text{s}$ • $V_{DD}\geq V_{DS}$, Starting $T_J=25^\circ\text{C}$
- Pulse Test : Pulse Width $\leq 1\text{ms}$ • $T_J\leq 125^\circ\text{C}$ & $|V_{GS}|<10\text{V}$
- Essentially Independent of Operating Temperature

Typical Characteristics

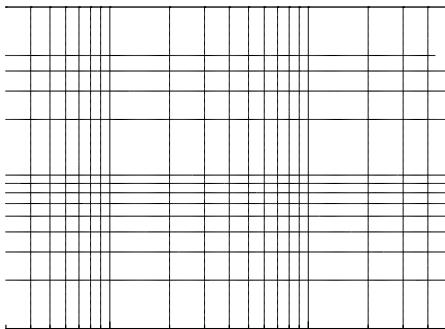


Figure 1. On Region Characteristics

Figure 2. Transfer Characteristics

Figure 3. On Resistance Variation vs
Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage
Variation with Source Current
and Temperature

Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

Fig 12. Gate Charge Test Circuit & Waveform

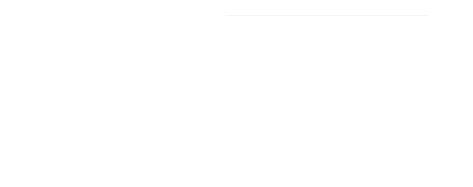


Fig 13. Resistive Switching Test Circuit & Waveforms

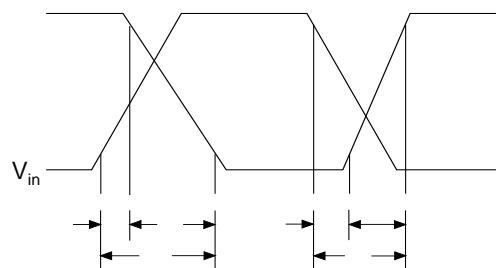
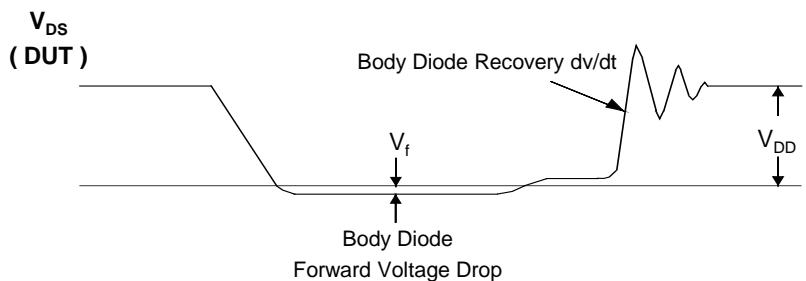
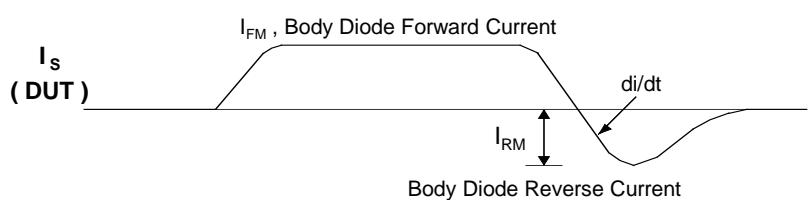
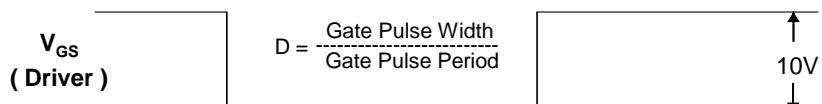
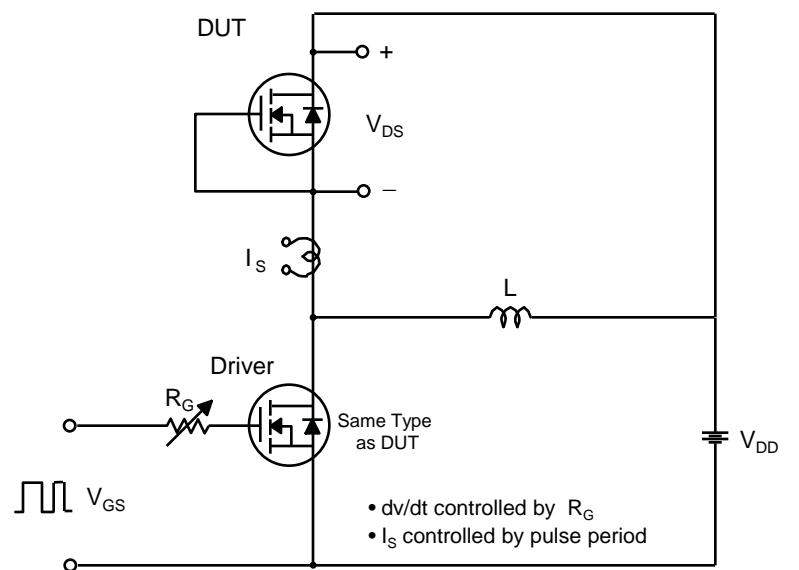
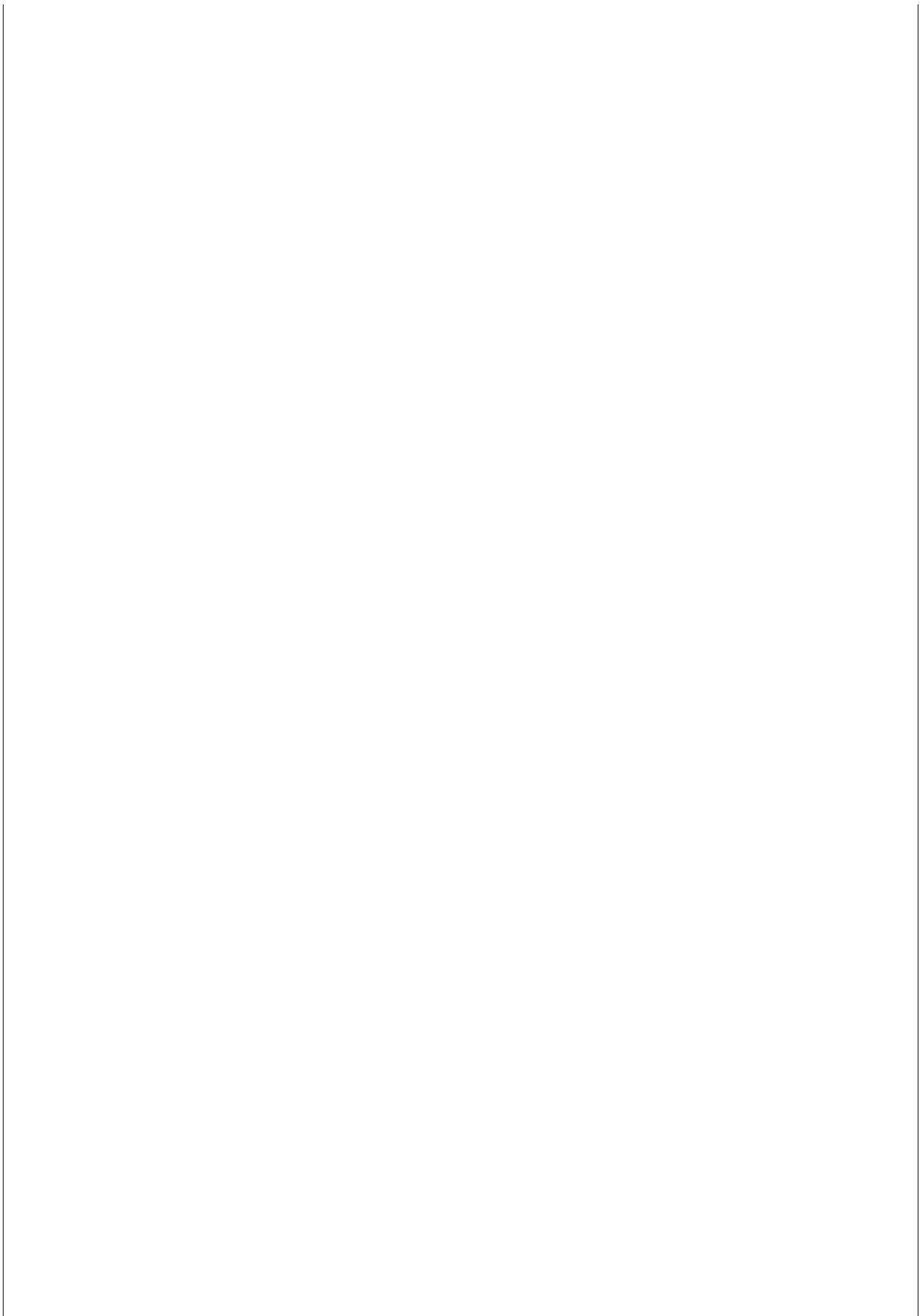


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

$$E_{AS} = \frac{1}{2} L_L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

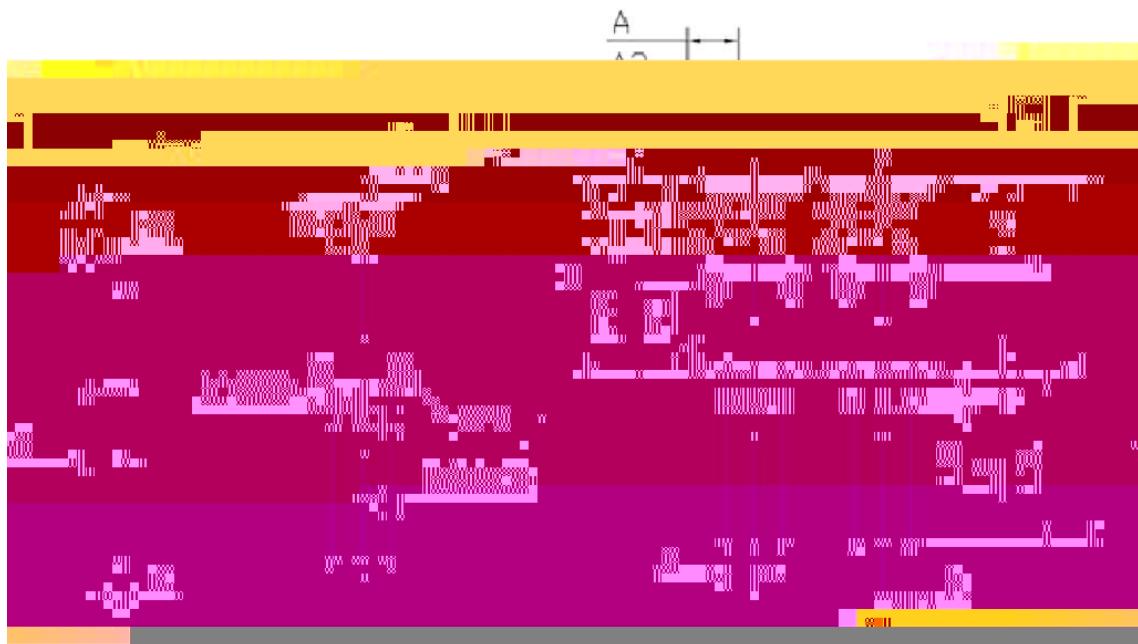
Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





Package Dimension

TO-220F (B)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300 REF.		0.051 REF.	
b	0.020	0.030	0.600	0.750
b1	0.045	0.051	1.150	1.300
c	0.750	0.020	0.030	0.600
d	0.583	0.598	14.800	15.200
e	0.106 REF.		2.540 REF.	
f	0.248 REF.		2.700 REF.	
g	0.087 REF.		6.300 REF.	
h1	0.020 REF.		0.200 REF.	
h2	0.031 REF.		0.600 REF.	
i1	1.300	0.033	0.071	1.400
i2	2.000	0.017	0.079	1.200
i3	13.8	0.512	0.643	13.0
j		0.276 REF.	14	7.000 REF.